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N-Channel 80 V (D-S) Super Junction MOSFET

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N-Channel MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R _{DS(on)} (mΩ)(TYP.)	I _D (A)	Q _g (TYP.)	
80	1.6 at V _{GS} = 10 V	290	155 nC	

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TO-247AC

FEATURES

- DT-TrenchPower MOSFET
- + 100 % $\rm R_g$ and UIS tested
- Improved dv/dt capability

APPLICATIONS

- Power supplies:
 - Uninterruptible power supplies
 - AC/DC switch-mode power supplies
 - Lighting
- Synchronous rectification
- DC/DC converter
- Motor drive switch
- Hard Switched and High Frequency Circuits

ABSOLUTE MAXIMUM RATINGS ($T_c = 25$ °C, unless otherwise noted)						
PARAMETER		LIMIT	UNIT			
Drain-Source Voltage		V _{DS}	80	V		
Gate-Source Voltage		V _{GS} ± 20		V		
Continuous Durin Current (T. 150 °C)	T _C = 25 °C		290			
Continuous Drain Current ($T_J = 150 \ ^{\circ}C$)	T _C = 100 °C	I _D	165			
Pulsed Drain Current (t = 100 µs)		I _{DM}	1200	A		
Avalanche Current	L = 0.1 mH	I _{AS}	170			
Single Avalanche Energy ^a		E _{AS}	1310	mJ		
Maximum Power Dissipation ^a	T _C = 25 °C	Р	420 ^b	W		
	T _C = 125 °C	– P _D	84 ^b			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C		

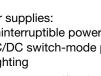
THERMAL RESISTANCE RATINGS				
PARAMETER		LIMIT	UNIT	
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	62	°C/W	
Junction-to-Case (Drain)	R _{thJC}	0.42	C/W	

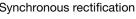
Notes

a. Duty cycle \leq 1 %.

b. See SOA curve for voltage derating.

c. When mounted on 1" square PCB (FR4 material).







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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static				•	•	
Drain-Source Breakdown Voltage	V _{DS}	V_{GS} = 0 V, I_D = 250 μ A	80	-	-	v
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1.2	-	2.5	
Gate-Body Leakage	I _{GSS}	$V_{DS}=0~V,~V_{GS}=\pm~20~V$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 80 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-	-	1	- μΑ
		V_{DS} = 64 V, V_{GS} = 0 V, T_{J} = 85 $^{\circ}\text{C}$	-	-	10	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}$	-	1.6	1.98	mΩ
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 3 \text{ A}$	-	18	-	S
Dynamic ^b				•		
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 40 V, f = 1 MHz	-	9750	-	pF
Output Capacitance	C _{oss}		-	2030	-	
Reverse Transfer Capacitance	C _{rss}		-	77	-	
Total Gate Charge ^c	Qg	$V_{DS} = 40 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$	-	155	-	nC
Gate-Source Charge ^c	Q _{gs}		-	32	-	
Gate-Drain Charge ^c	Q _{gd}		-	73	-	
Gate Resistance	R _g	f = 1 MHz	-	1.0	-	Ω
Turn-On Delay Time ^c	t _{d(on)}		-	20	-	- ns
Rise Time ^c	t _r	$V_{DD} = 40 \text{ V}, \text{ R}_{\text{I}} = 1.67 \Omega$	-	16	-	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 30 \text{ A}, V_{\text{GEN}} = 10 \text{ V}, \text{ R}_g = 1 \Omega$	-	47	-	
Fall Time ^c	t _f		-	55	-	
Drain-Source Body Diode Ratings ar	d Characteri	stics ^b (T _C = 25 °C)				
Pulsed Current (t = 100 µs)	I _{SM}		-	-	1200	А
Forward Voltage ^a	V _{SD}	$I_F = 30 \text{ A}, V_{GS} = 0 \text{ V}$	-	-	1.0	V
Reverse Recovery Time	t _{rr}		-	105	-	ns
Peak Reverse Recovery Charge	I _{RM(REC)}	I _F = 30 A, di/dt = 100 A/μs	-	7	-	Α
Reverse Recovery Charge	Q _{rr}		-	310	-	nC

Notes

a. Pulse test; pulse width $\leq 300~\mu\text{s},$ duty cycle $\leq 2~\%.$

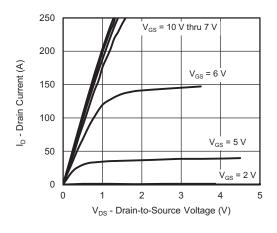
b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

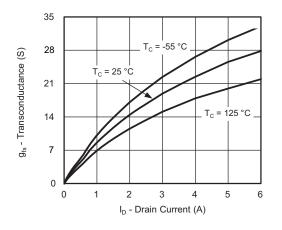
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



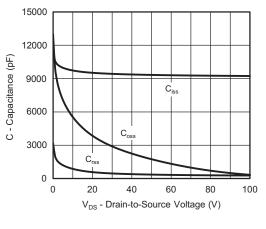
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



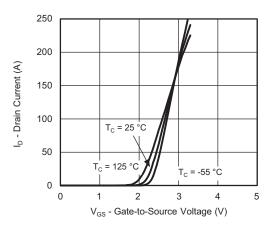
Output Characteristics



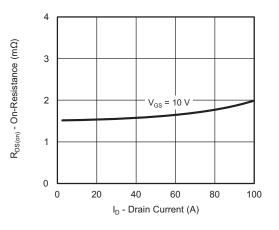
Transconductance



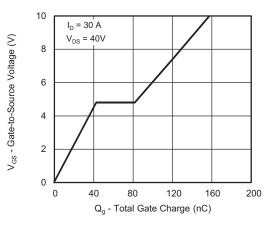
Capacitance



Transfer Characteristics



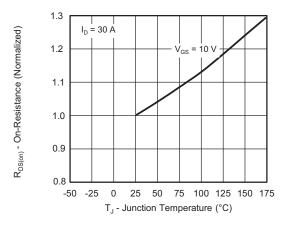
On-Resistance vs. Drain Current



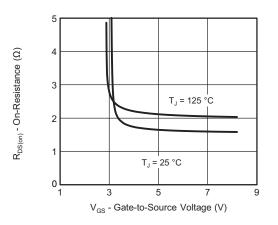
Gate Charge



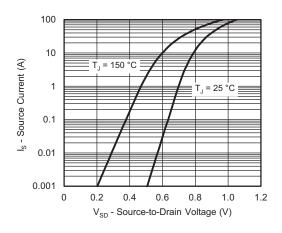
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



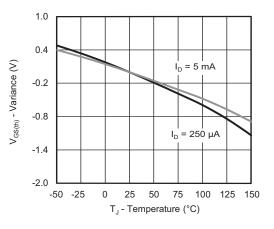
On-Resistance vs. Junction Temperature



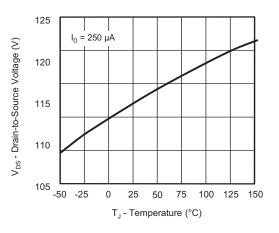
On-Resistance vs. Gate-to-Source Voltage



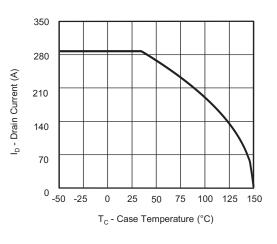
Source Drain Diode Forward Voltage



Threshold Voltage

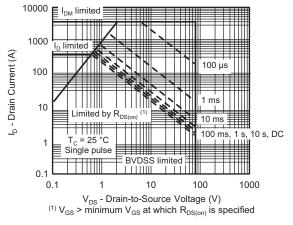


Drain Source Breakdown vs. Junction Temperature

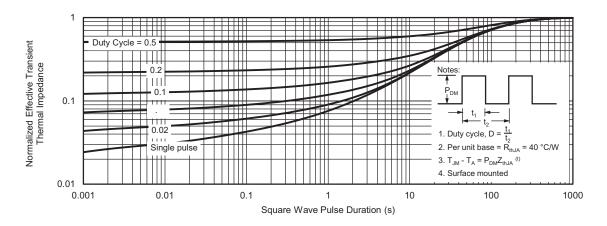


Current De-Rating

THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



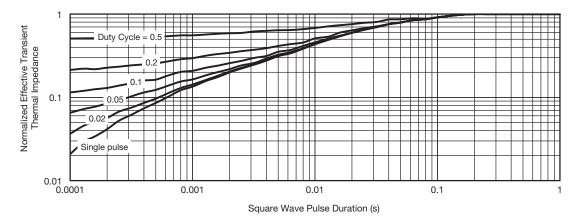
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



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